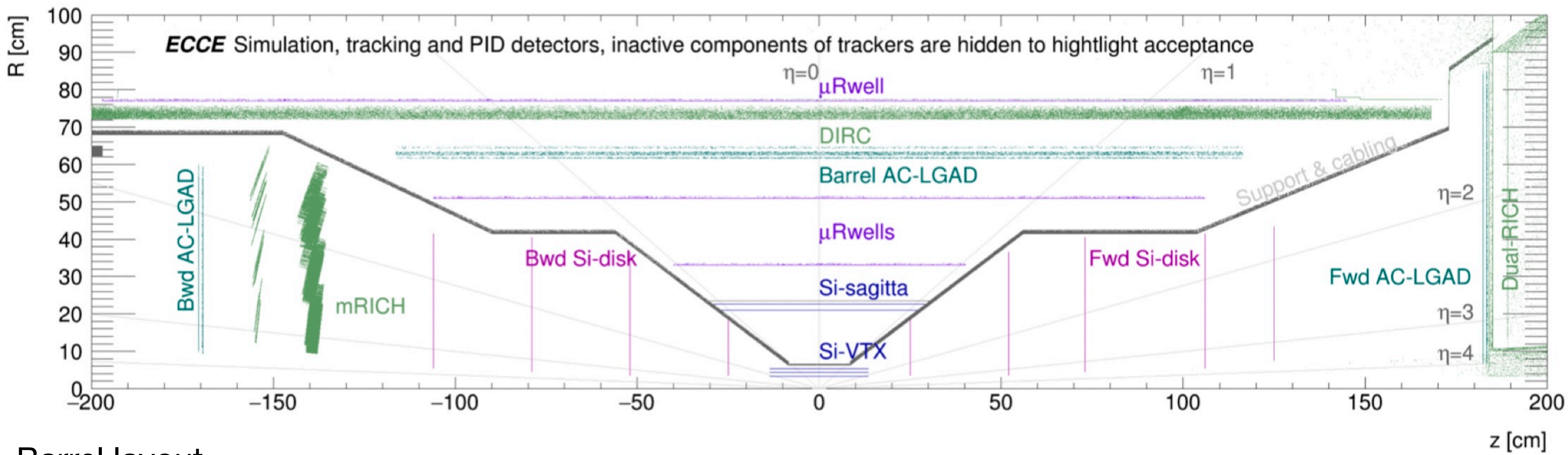


Optimizing the EIC tracker configuration (Continuation)

Rey Cruz-Torres
RNC EIC Meeting
July 5th, 2022

Barrel

The ECCE configuration



Barrel layout

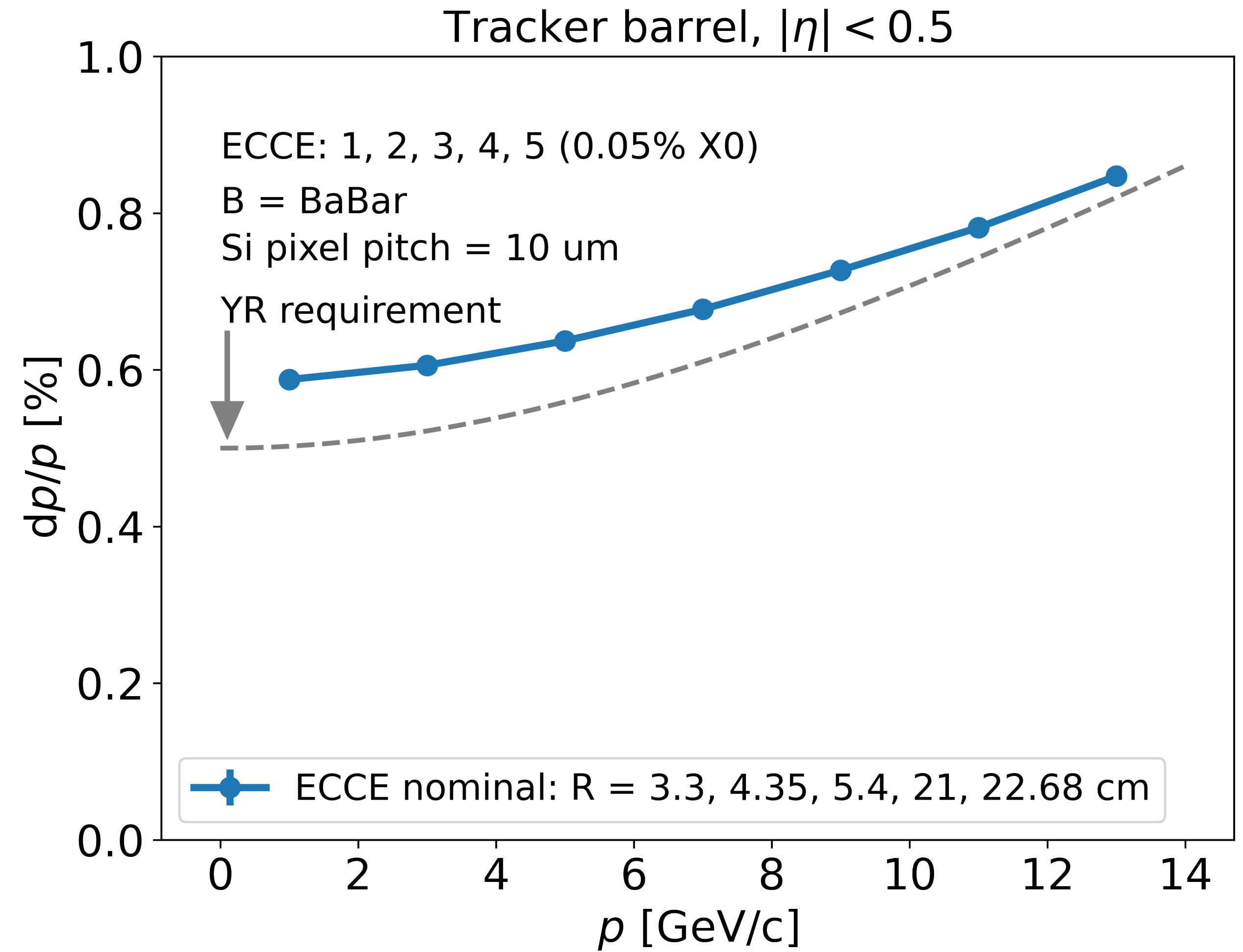
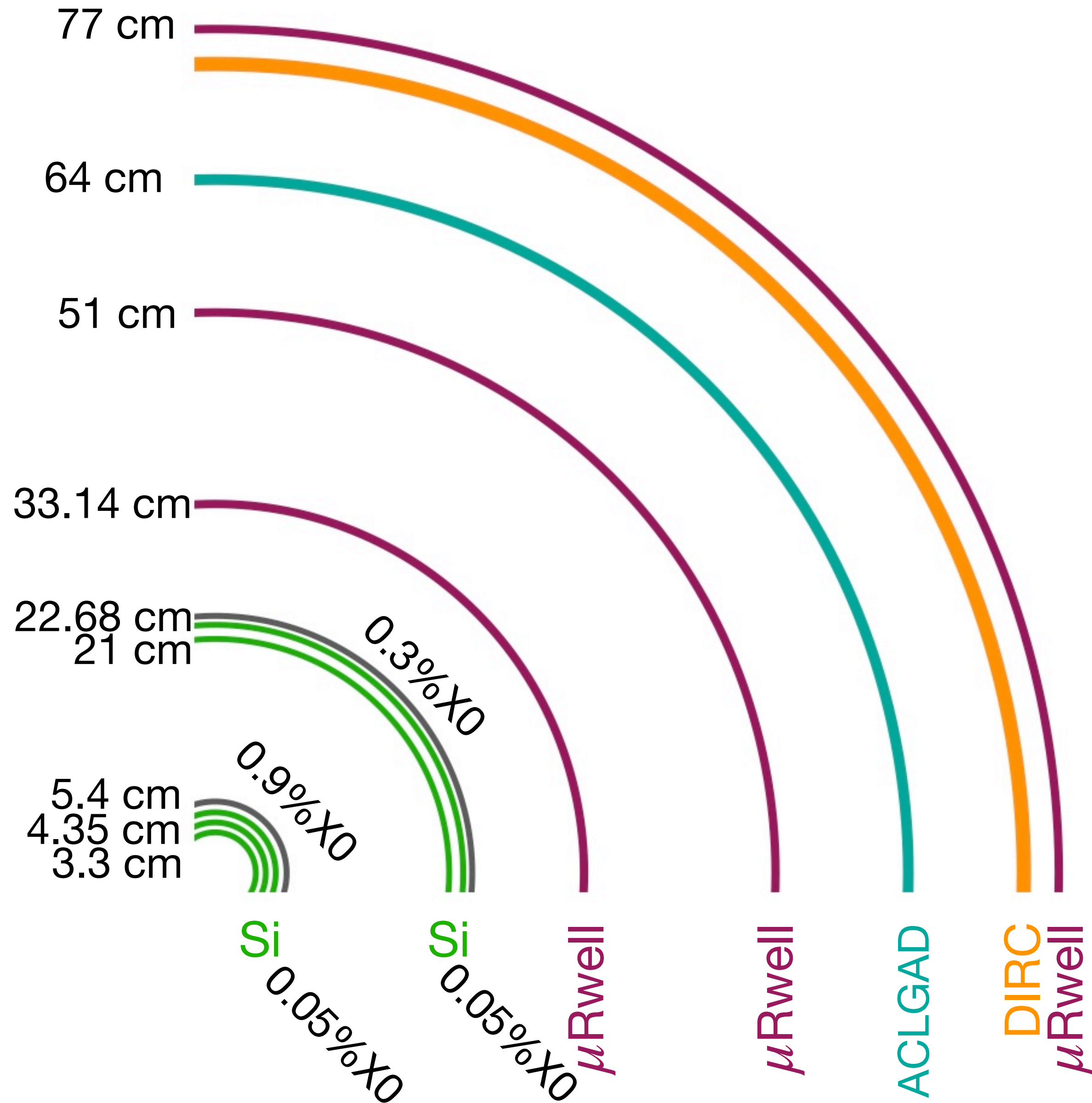
Si	r (cm)	length (cm)	X
1	3.3	27	0.05
2	4.35	27	0.05
3	5.4	27	0.05
4	21	54	0.05
5	22.68	58	0.05

	r (cm)	length (cm)	point res
uRwell1	33.14	80.16	55 um
uRwell2	51	212	55 um
ACLGAD	64	140	30 um
uRwell3	77.0175	342	55 um

Pitch = 10 um

And also two support cylinders:
- r = 6.3 cm, 0.9% X0
- r = 23.5 cm, 0.3% X0

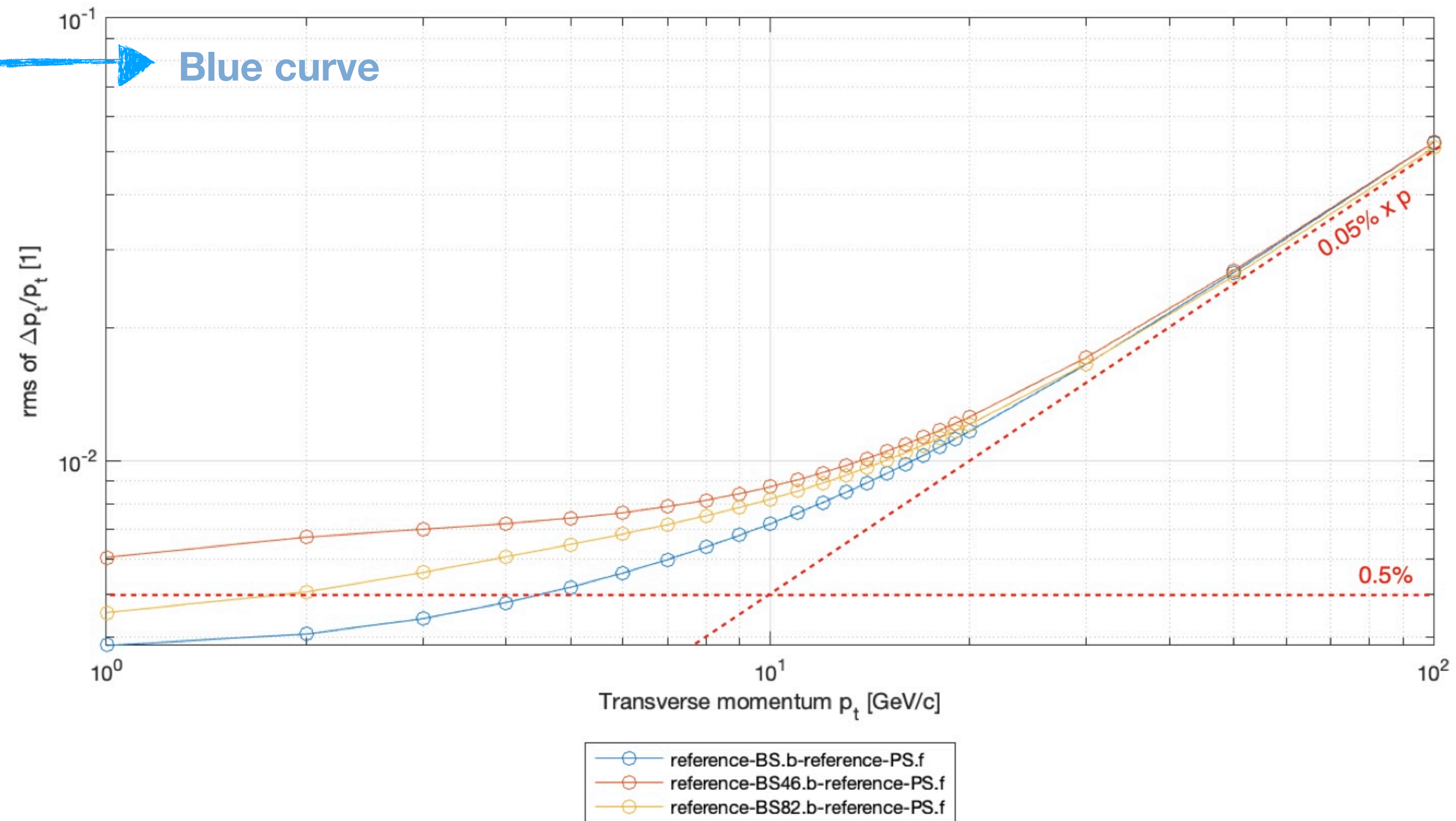
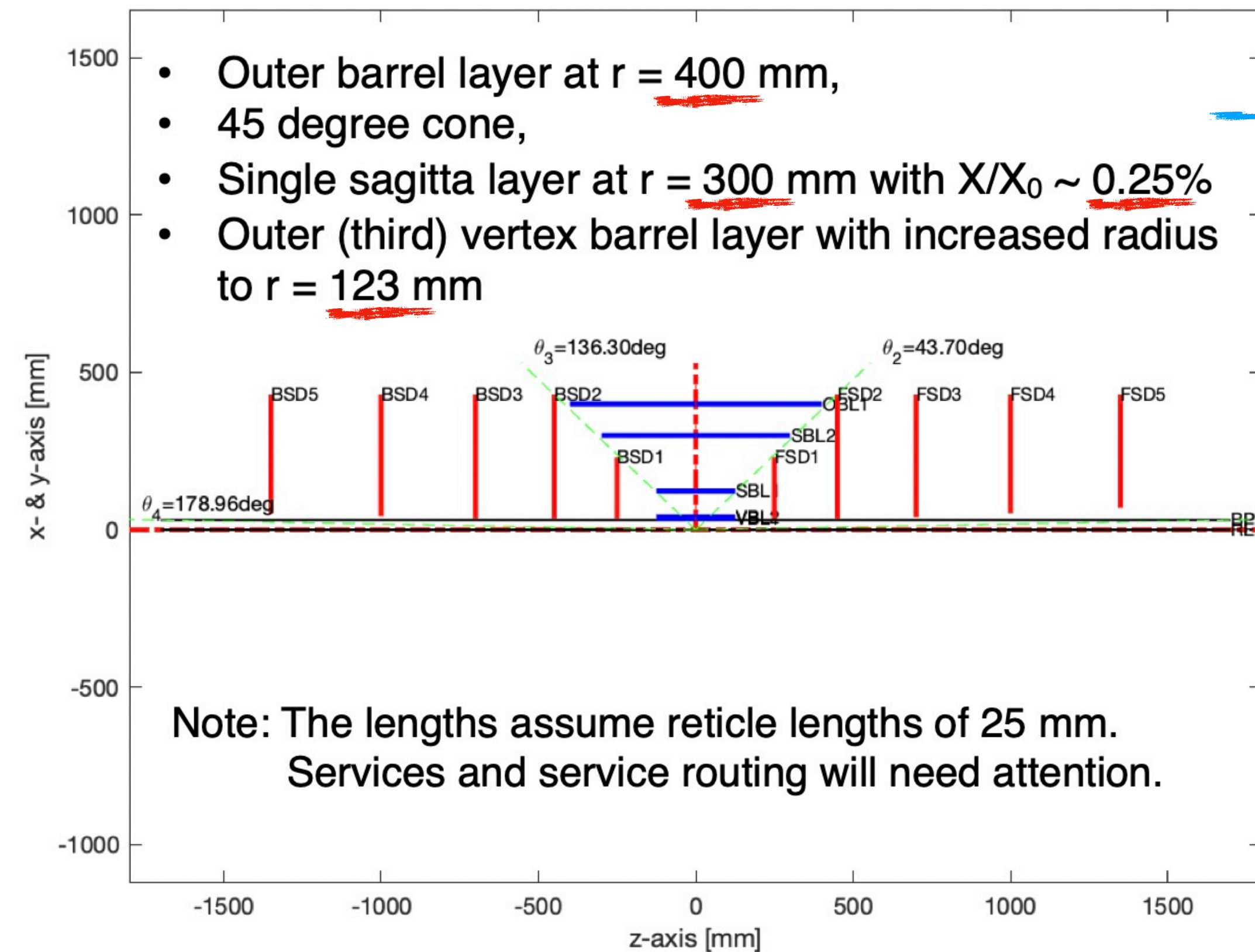
Momentum resolution performance of ECCE Barrel



Barrel optimization with fast simulations

Work by E. Sichtermann

See slides from <https://conferences.lbl.gov/event/974/>



It seems sensible to simulate this in Fun4All already now, even though other changes will be needed. Volunteers ;-)?

New proposed barrel configuration

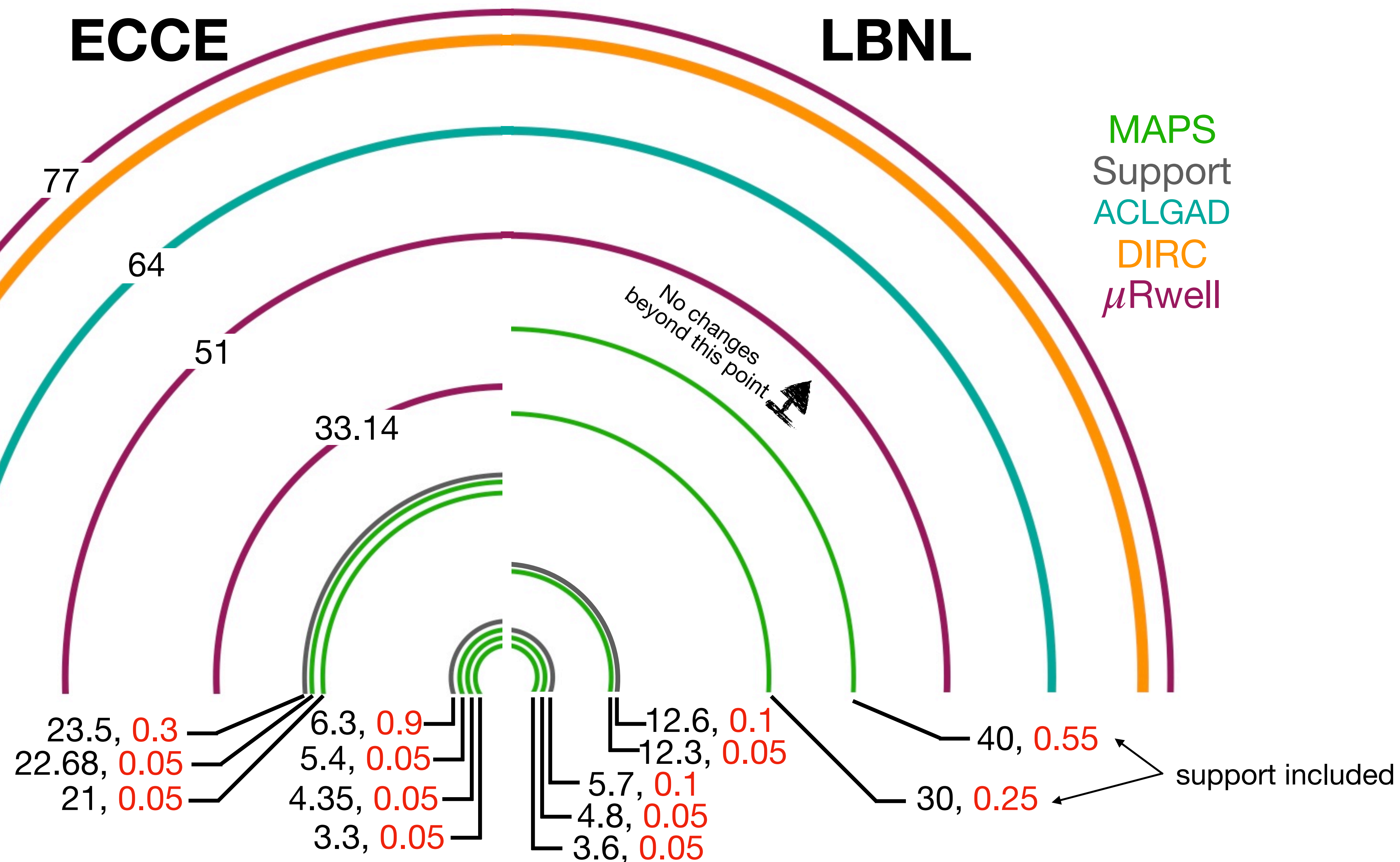
All black numbers
are radii in units
of cm

All red numbers
are material
budgets in units
of % X0

ECCE

LBNL

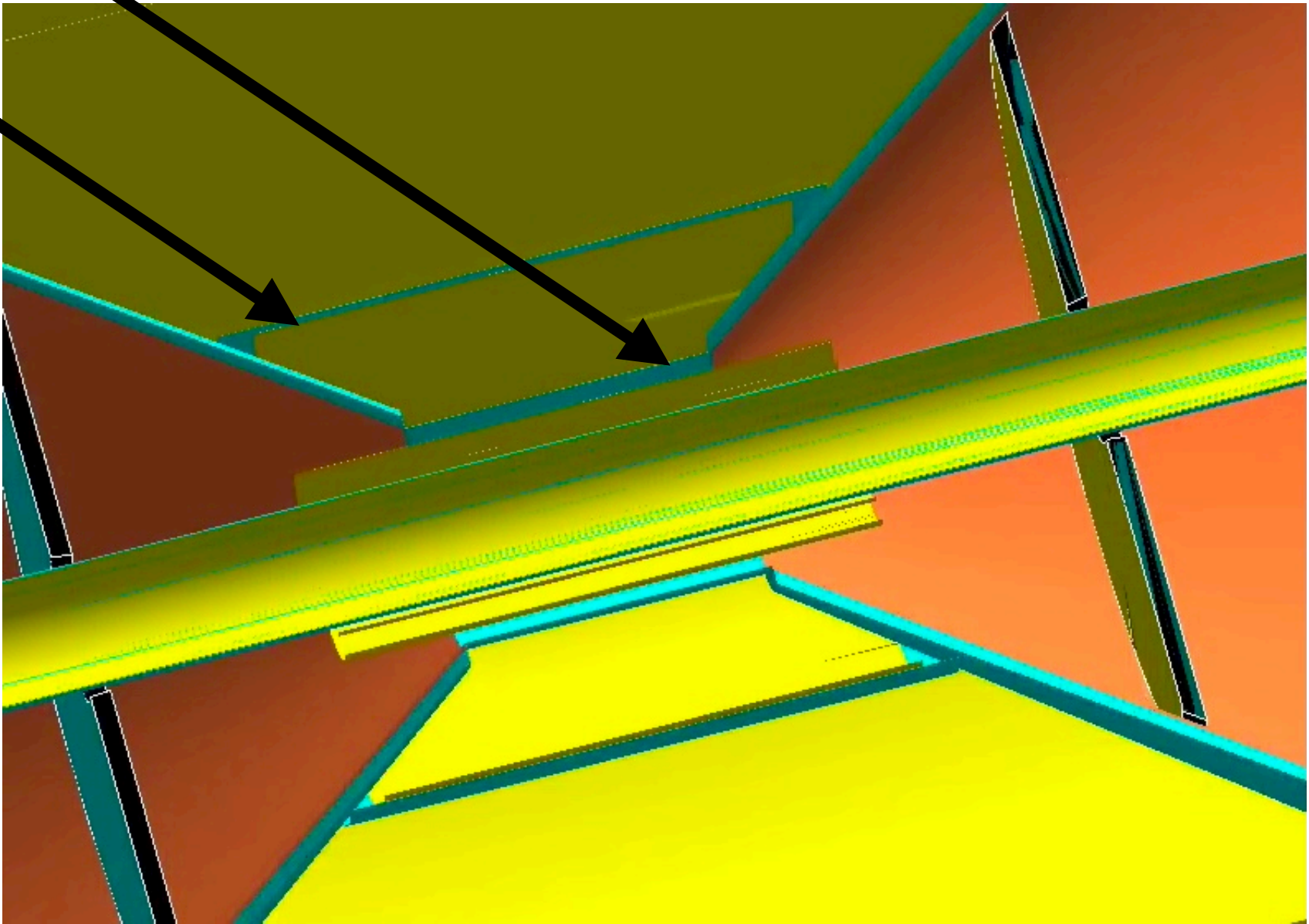
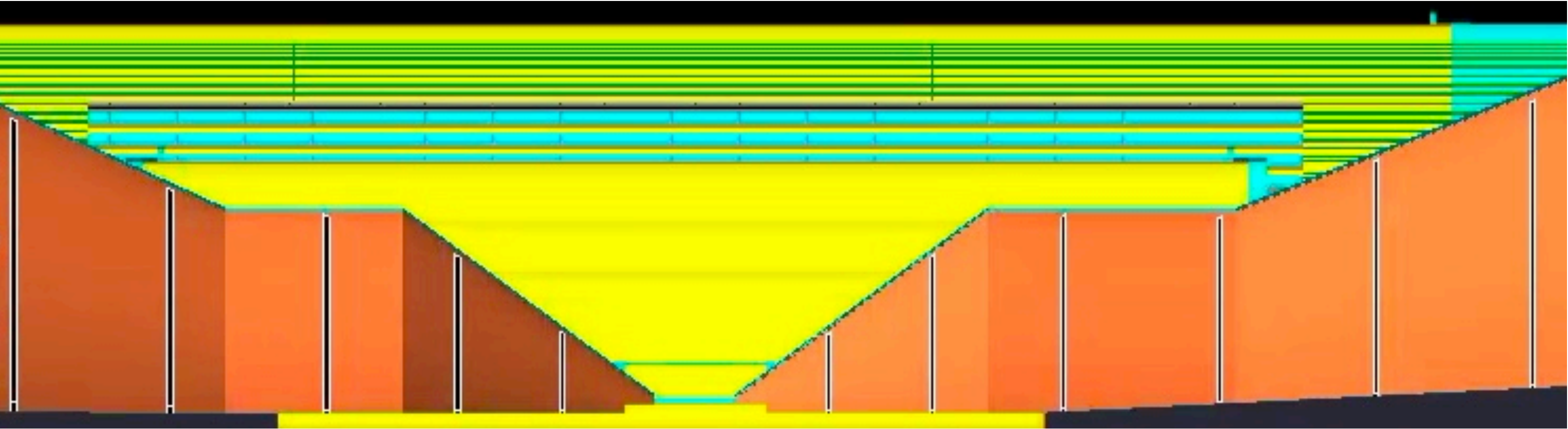
MAPS
Support
ACLGAD
DIRC
 μ Rwell



New proposed barrel configuration

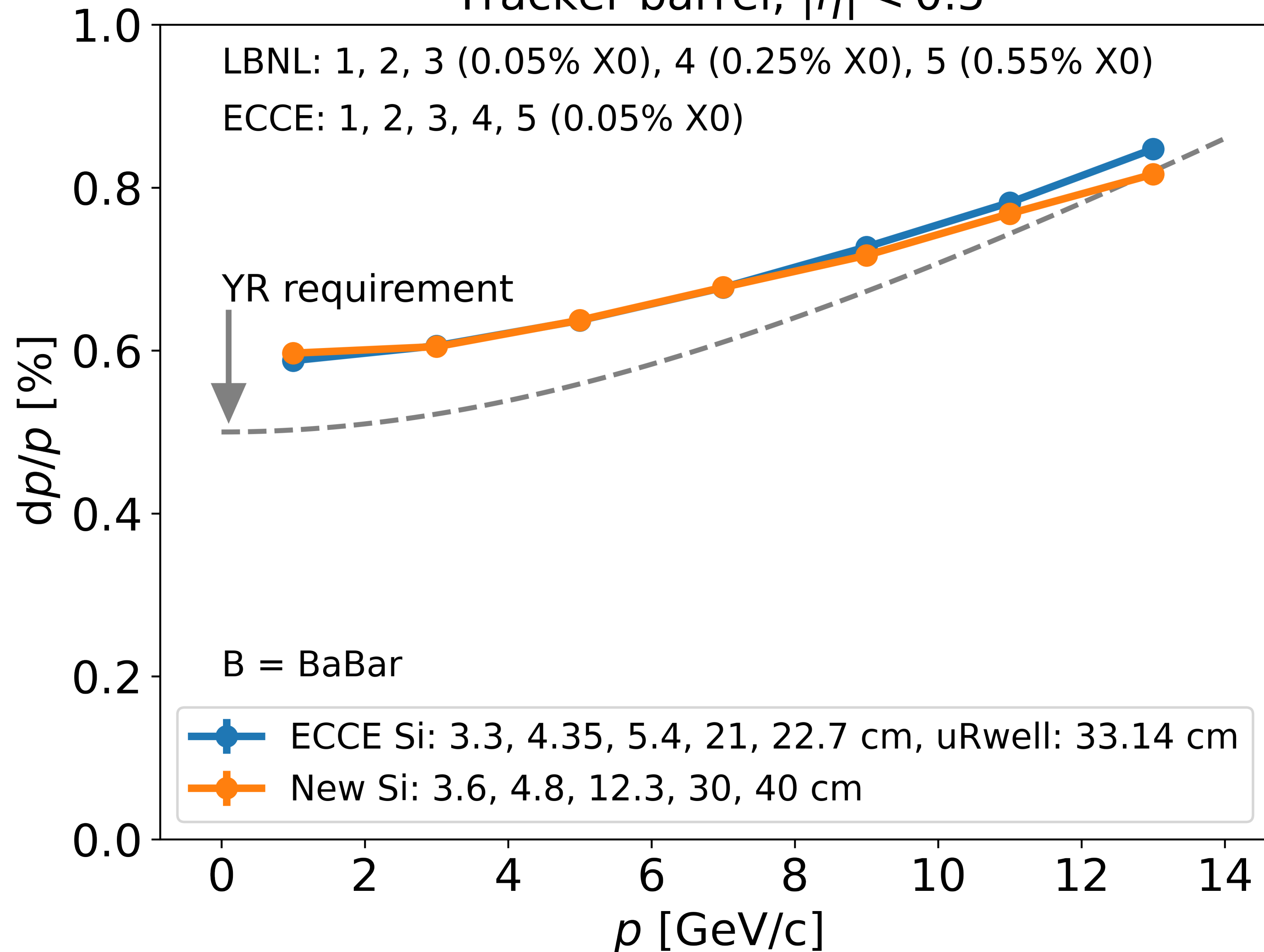
	r (cm)	length (cm)	X/X0	A (m ²)
1	3.6	27	0.05%	0.061
2	4.8	27	0.05%	0.081
Support	5.7	15.4	0.1%	
3	12.3	27	0.05%	0.21
Support	12.6	30.6	0.1%	
4	30	77	0.25%	1.5
5	40	104	0.55%	2.6

	r (cm)	length (cm)	point res
uRwell2	51	212	55 um
ACLGAD	64	140	30 um
uRwell3	77.0175	342	55 um



New proposed barrel configuration

Tracker barrel, $|\eta| < 0.5$



Both settings have:
uRwell $R = 51, 77$ cm
ACLGAD $R = 64$ cm

ECCE has support layer:
 $R = 6.3$ (0.9%), 23.5 cm (0.3%X0)

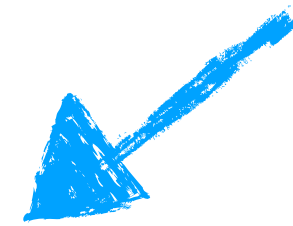
New has support layer:
 $R = 5.7$ (0.1%), 12.6 cm (0.1%X0)

MAPS $\sigma = 10/\sqrt{12} \mu\text{m}$
 $\mu\text{Rwells } \sigma = 55 \mu\text{m}$
ACLGAD $\sigma = 30 \mu\text{m}$

Can we improve this performance even further?

Can we improve this performance even further?

Yes



Reduction of material
budget near sagitta

Expansion of highest-R
silicon layer

Targeting the constant term

Momentum Resolution Performance

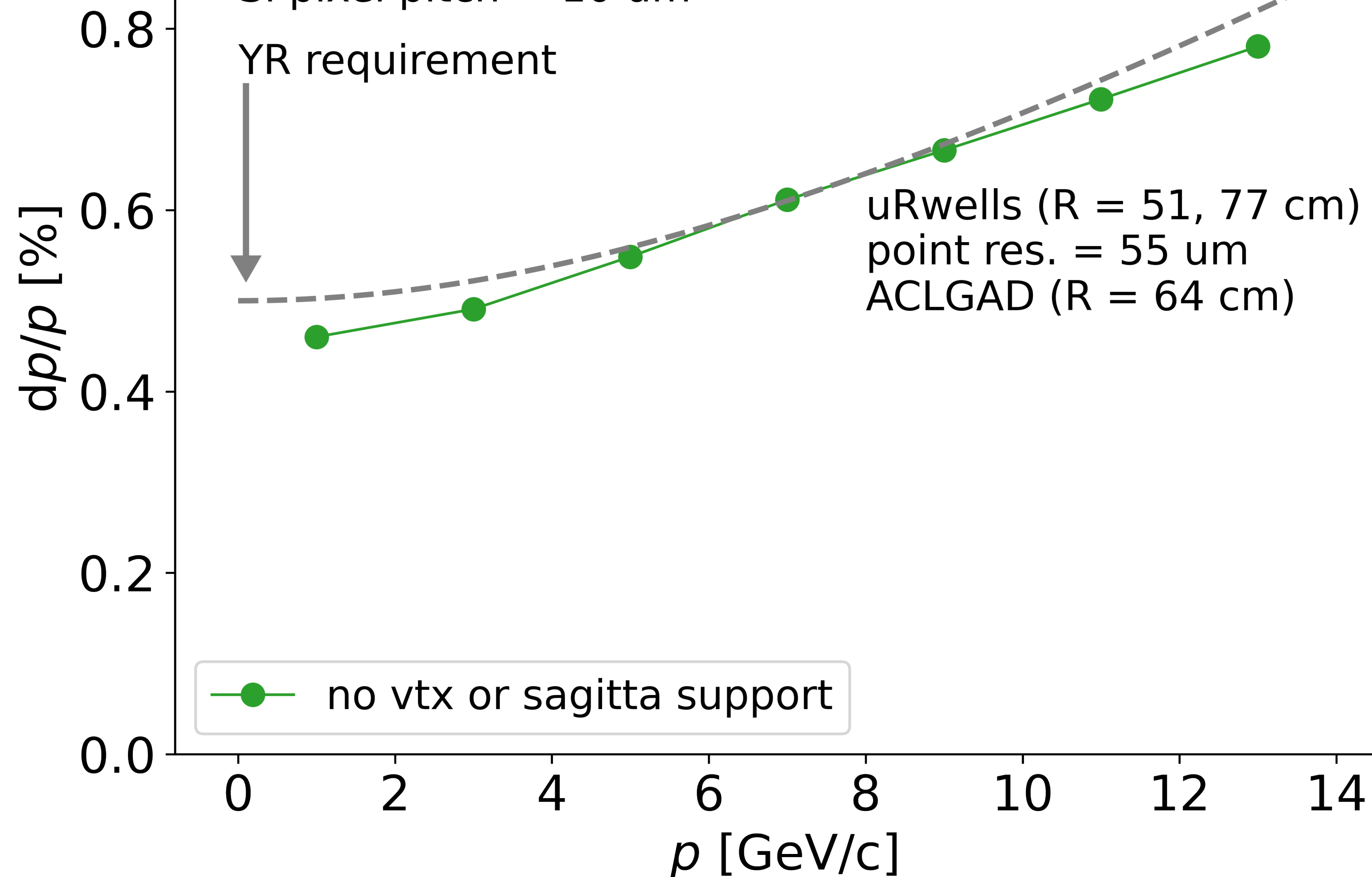
Tracker barrel, $|\eta| < 0.5$

LBL: 1, 2, 3 (0.05% X0), 4 (0.25% X0), 5 (0.55% X0)

B = BaBar

Si pixel pitch = 10 μm

YR requirement



Performance below requirement when innermost three layers are not supported



Momentum Resolution Performance

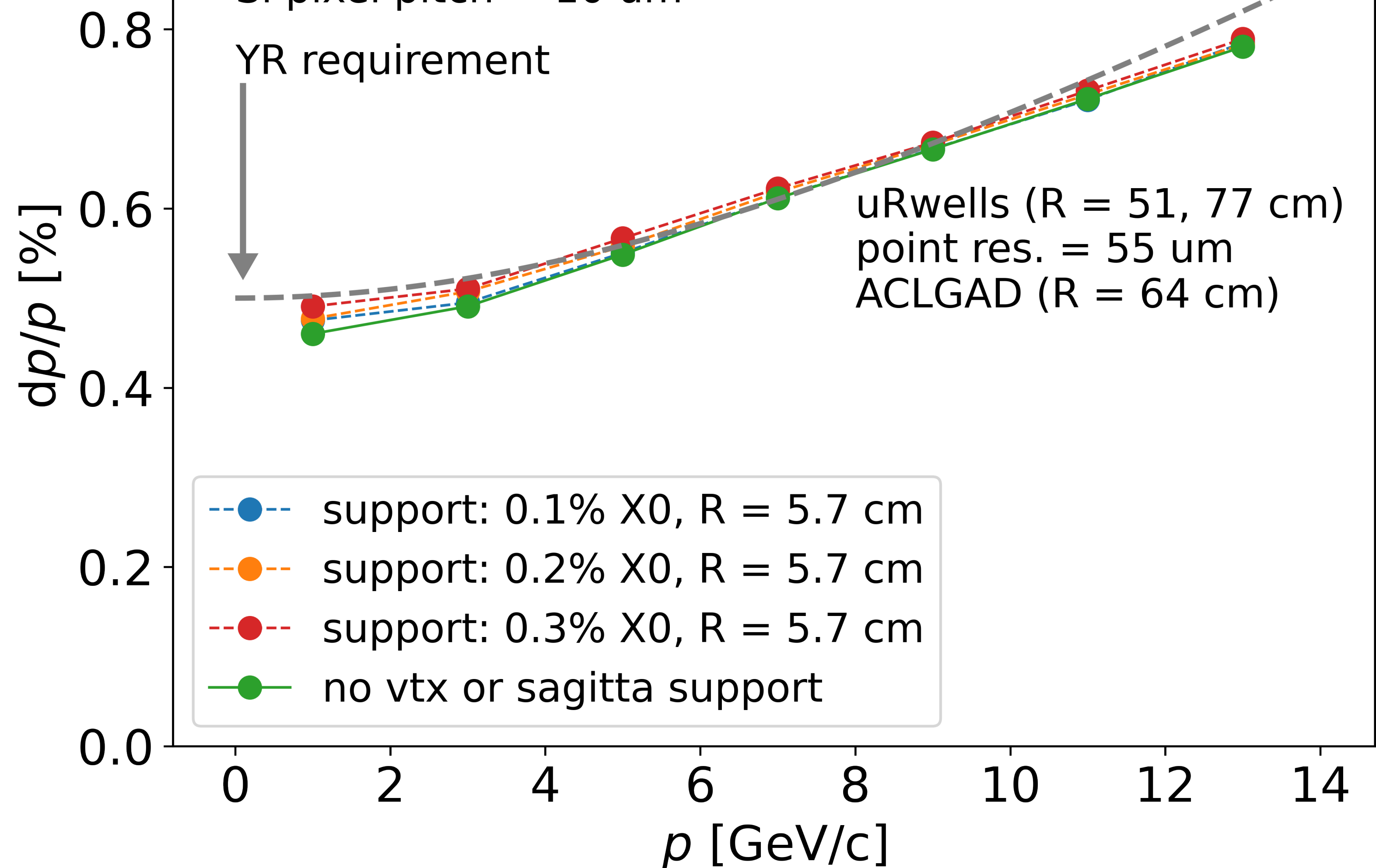
Tracker barrel, $|\eta| < 0.5$

LBL: 1, 2, 3 (0.05% X_0), 4 (0.25% X_0), 5 (0.55% X_0)
B = BaBar
Si pixel pitch = 10 μm

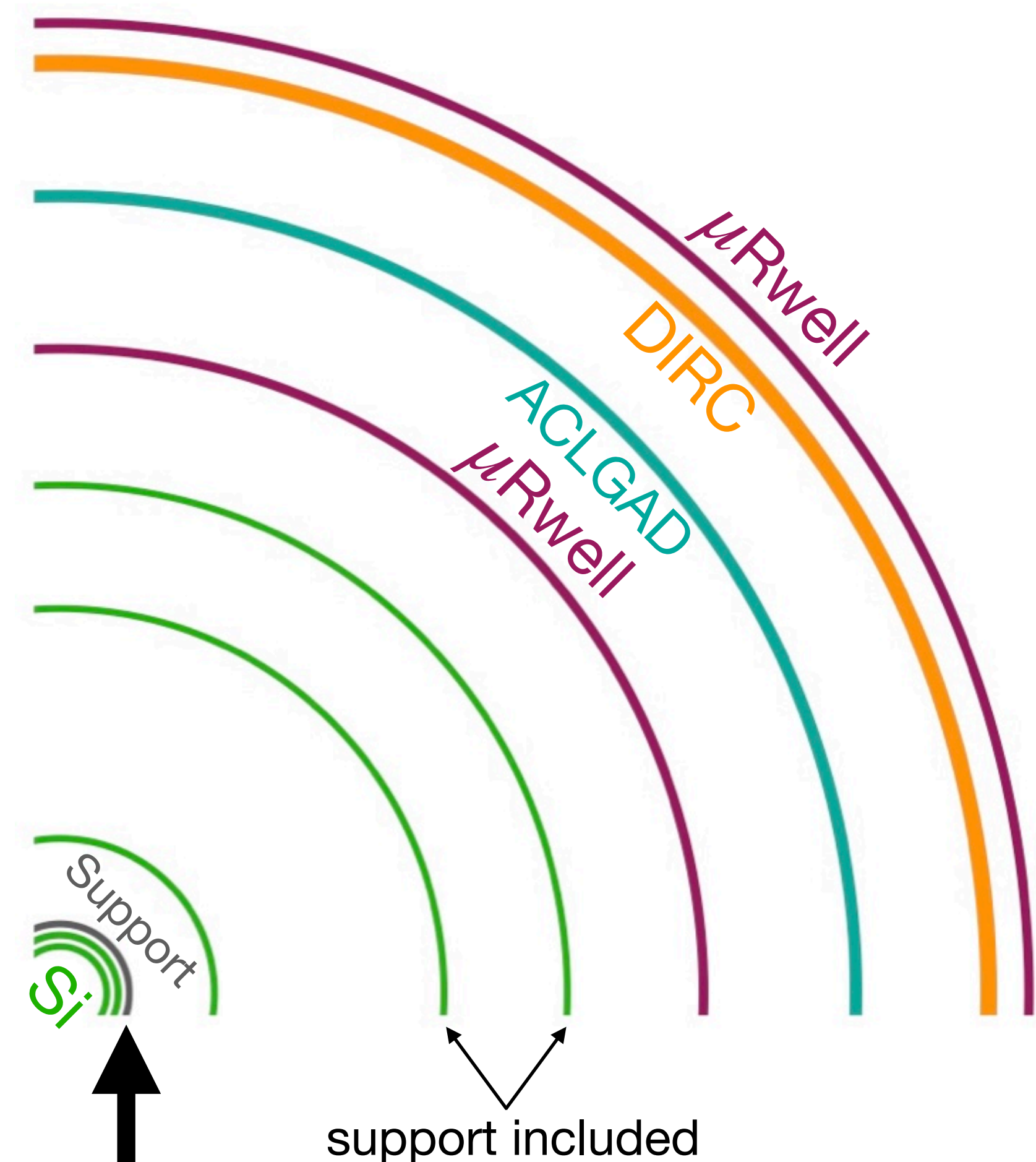
YR requirement

uRwells ($R = 51, 77 \text{ cm}$)
point res. = 55 μm
ACLGAD ($R = 64 \text{ cm}$)

- support: 0.1% X_0 , $R = 5.7 \text{ cm}$
- support: 0.2% X_0 , $R = 5.7 \text{ cm}$
- support: 0.3% X_0 , $R = 5.7 \text{ cm}$
- no vtx or sagitta support

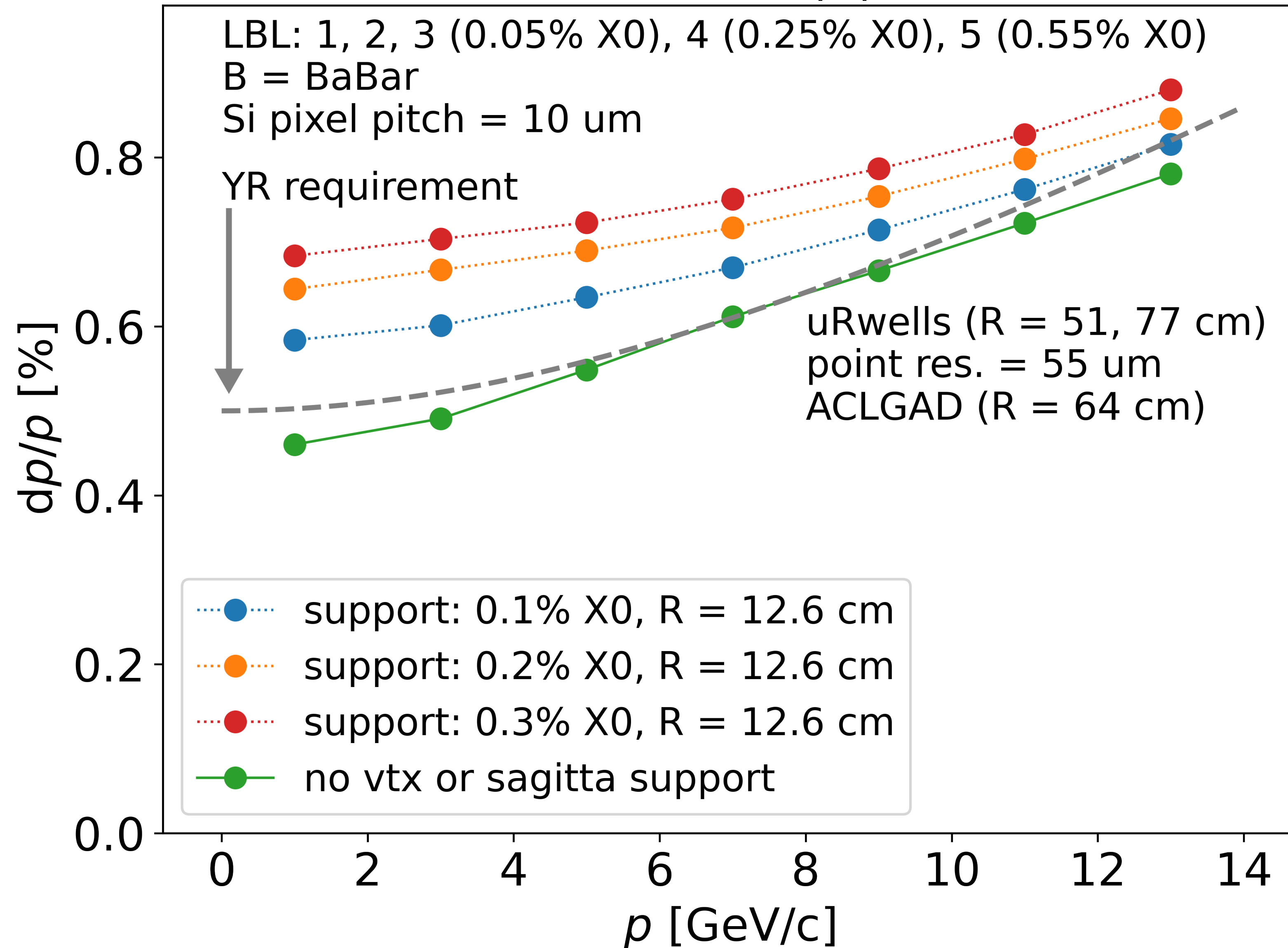


Material near innermost two layers doesn't significantly degrade dp/p

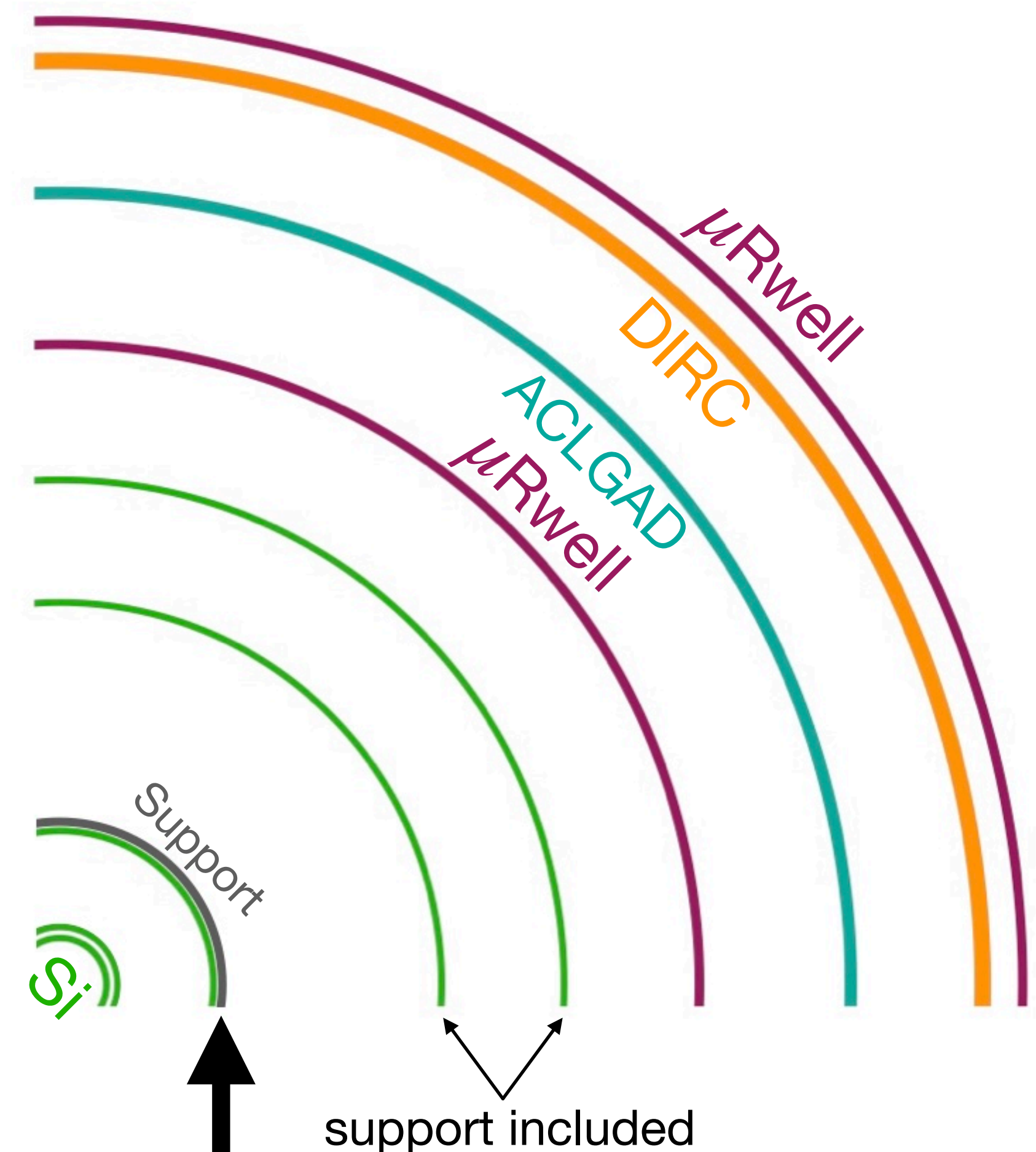


Momentum Resolution Performance

Tracker barrel, $|\eta| < 0.5$

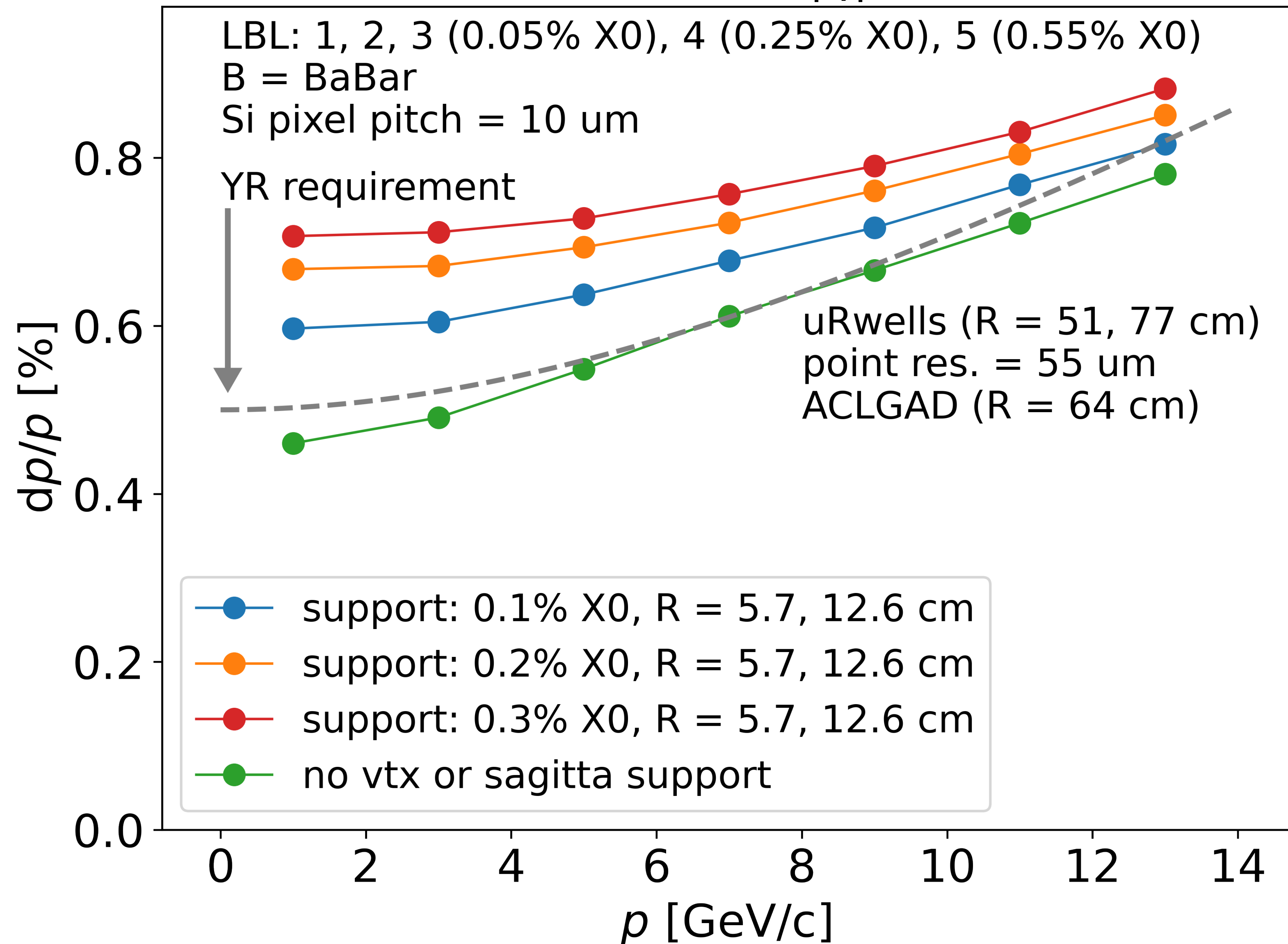


Material near sagitta
 significantly degrades dp/p

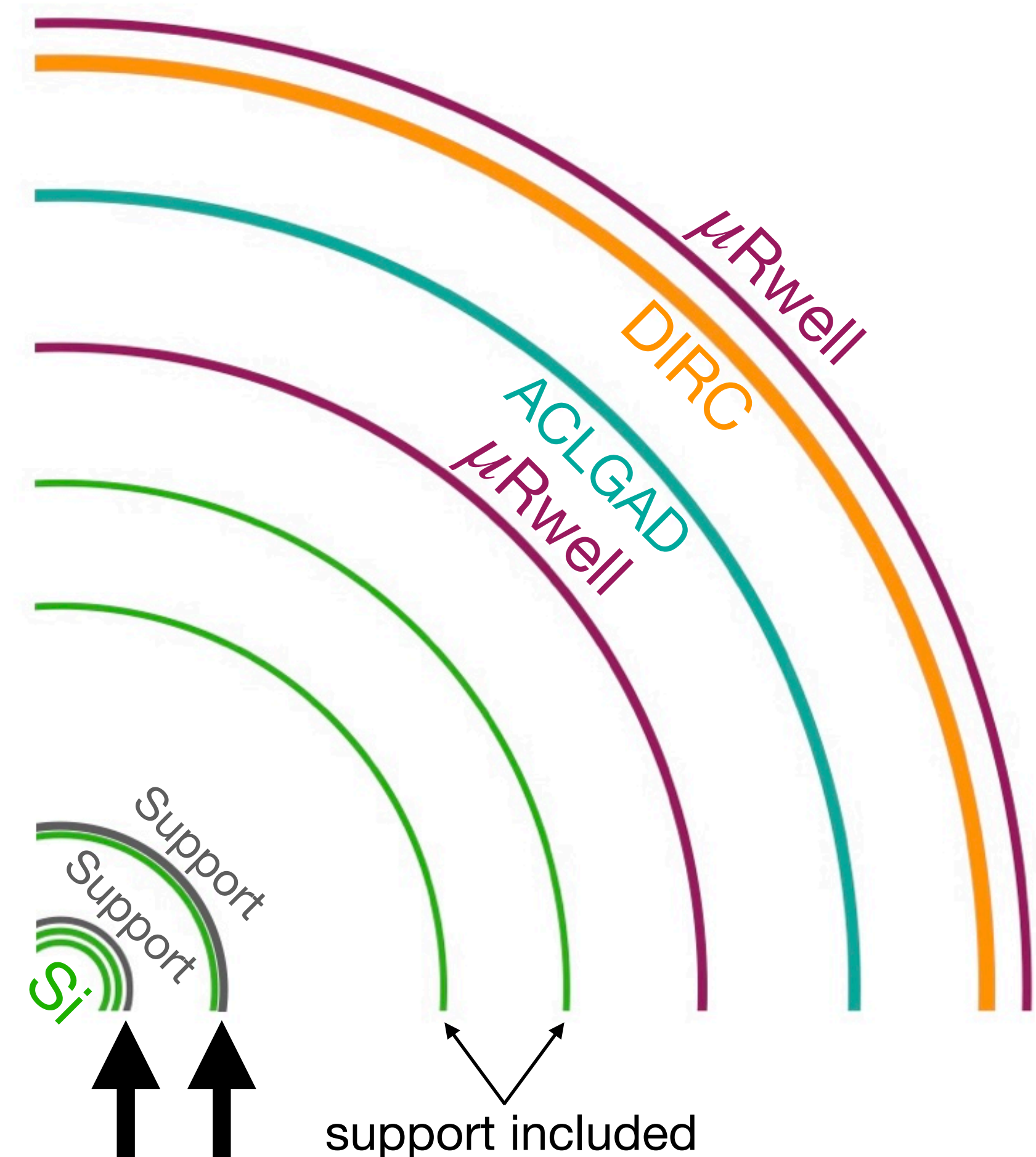


Momentum Resolution Performance

Tracker barrel, $|\eta| < 0.5$



The performance with both layers is dominated by the support near the sagitta



Can we improve this performance even further?

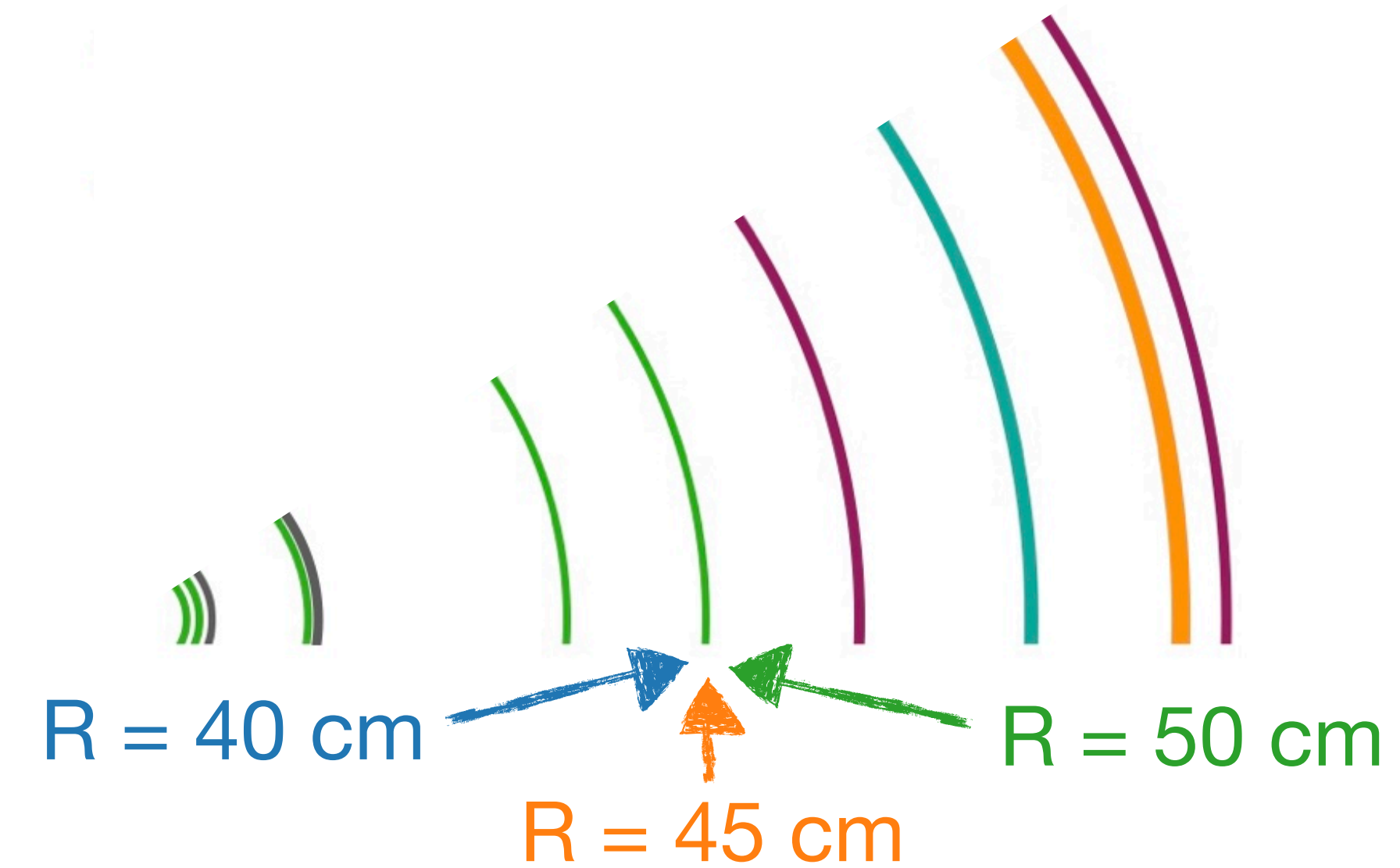
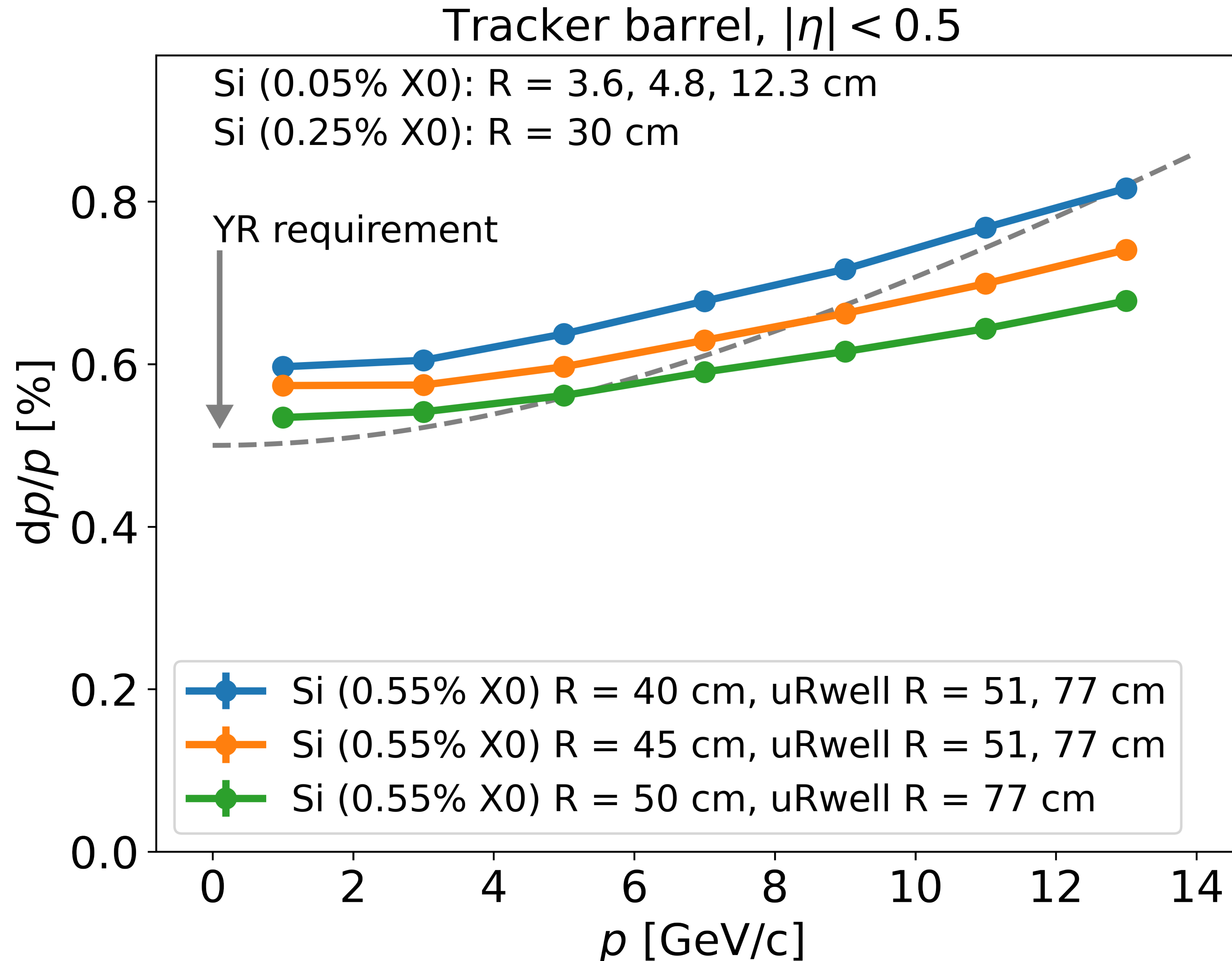
Yes

Reduction of material
budget near sagitta

Expansion of highest-R
silicon layer

Targeting the linear term

Impact from expanding radius of outermost silicon layer



The larger the radius the better the dp/p performance (and the larger the area)

MAPS $\sigma = 10/\sqrt{12} \mu\text{m}$
 $\mu\text{Rwells } \sigma = 55 \mu\text{m}$
 ACLGAD $\sigma = 30 \mu\text{m}$

B = BaBar

dp/p impact of MPGDs in the barrel

dp/p impact from barrel MPGDs

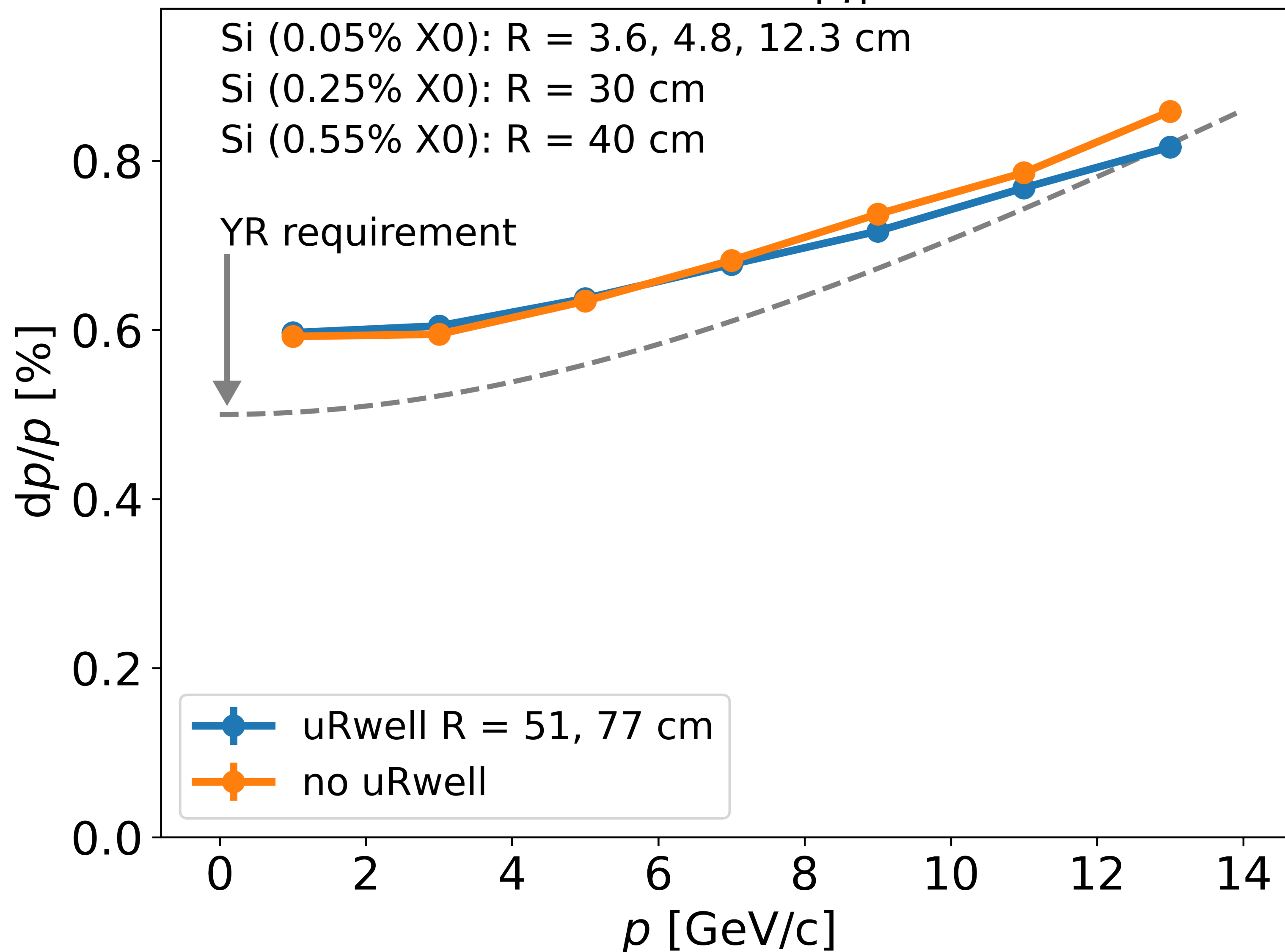
Tracker barrel, $|\eta| < 0.5$

Si (0.05% X0): $R = 3.6, 4.8, 12.3$ cm

Si (0.25% X0): $R = 30$ cm

Si (0.55% X0): $R = 40$ cm

YR requirement



Barrel MPGDs (as specified in this configuration) only has some dp/p-resolution impact in the higher-momentum regime.

However, this is not the only figure of merit and, when simulations with backgrounds are carried out, these layers may have a larger impact

MAPS $\sigma = 10/\sqrt{12} \mu\text{m}$

μ Rwells $\sigma = 55 \mu\text{m}$

ACLGAD $\sigma = 30 \mu\text{m}$

B = BaBar